BGA
Commercial Temp
Industrial Temp

1M x 8
8Mb Asynchronous SRAM

8, 10, 12 ns
3.3 V V_{DD}

Features

- Fast access time: 8, 10, 12 ns
- CMOS low power operation: 240/190/170 mA at minimum cycle time
- Single 3.3 V ± 0.3 V power supply
- All inputs and outputs are TTL-compatible
- Fully static operation
- Industrial Temperature Option: –40° to 85°C
- 14 mm x 22 mm, 119-bump, 1.27 mm Pitch Ball Grid Array package

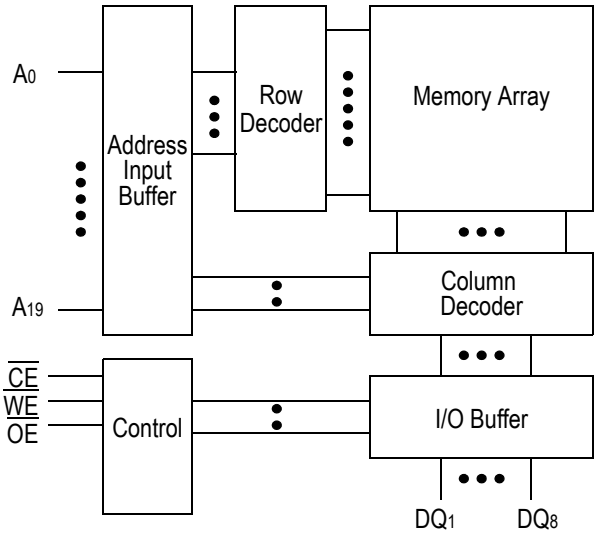
Description

The GS78108A is a high speed CMOS Static RAM organized as 1,048,576-words by 8-bits. Static design eliminates the need for external clocks or timing strobes. The GS78108operates on a single 3.3 V power supply, and all inputs and outputs are TTL-compatible. The GS7810A8 is available in a 14 mm x 22 mm BGA package.

Pin Descriptions

Symbol	Description
A_0 to A_{19}	Address input
DQ_1 to DQ_8	Data input/output
$\overline{CE}$	Chip enable input
$\overline{WE}$	Write enable input
$\overline{OE}$	Output enable input
V_{DD}	+3.3 V power supply
V_{SS}	Ground
NC	No connect

Block Diagram



1M x 8 Async SRAM in Bump, 14x22mm BGA

Top View

	1	2	3	4	5	6	7
A	NC	A_{15}	A_{14}	A_{16}	A_{13}	A_{12}	NC
B	NC	A_{11}	A_{10}	$\overline{CE}$	A_9	A_8	NC
C	NC	NC	V_{DD}, NC	A_{17}	V_{SS}, NC	NC	NC
D	NC	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	NC
E	NC	NC	V_{DD}	V_{SS}	V_{DD}	NC	NC
F	NC	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	NC
G	DQ_1	NC	V_{DD}	V_{SS}	V_{DD}	NC	DQ_5
H	DQ_2	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	DQ_6
J	V_{DD}	V_{SS}	V_{DD}	V_{SS}	V_{DD}	V_{SS}	V_{DD}
K	DQ_3	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	DQ_7
L	DQ_4	NC	V_{DD}	V_{SS}	V_{DD}	NC	DQ_8
M	NC	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	NC
N	NC	NC	V_{DD}	V_{SS}	V_{DD}	NC	NC
P	NC	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	NC
R	NC	NC	NC	NC	NC	NC	NC
T	NC	A_7	A_6	$\overline{WE}$	A_5	A_4	NC
U	A_{18}	A_3	A_2	$\overline{OE}$	A_1	A_0	A_{19}

Note: Bumps 3C and 5C are actually NC's but should be wired 3C = V_{DD} and 5C = V_{ss} to assure compatibility with future versions.

Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	DQ_1 to DQ_8	V_{DD} Current
H	X	X	Not Selected	ISB1, ISB2
L	L	H	Read	—
L	X	L	Write	I_{DD}
L	H	H	High Z	—

Note: X: "H" or "L"

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply Voltage	V_{DD}	–0.5 to +4.6	V
Input Voltage	V_{IN}	–0.5 to V_{DD} +0.5 (≤ 4.6 V max.)	V
Output Voltage	V_{OUT}	–0.5 to V_{DD} +0.5 (≤ 4.6 V max.)	V
Allowable power dissipation	PD	1.5	W
Storage temperature	T_{STG}	–55 to 150	°C

Note:
Permanent device damage may occur if Absolute Maximum Ratings are exceeded. Functional operation shall be restricted to Recommended Operating Conditions. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage for -8/10/12	V_{DD}	3.0	3.3	3.6	V
Input High Voltage	V_{IH}	2.0	—	V_{DD} +0.3	V
Input Low Voltage	V_{IL}	–0.3	—	0.8	V
Ambient Temperature, Commercial Range	T_{Ac}	0	—	70	°C
Ambient Temperature, Industrial Range	T_{Ai}	–40	—	85	°C

Notes:
1. Input overshoot voltage should be less than V_{DD} +2 V and not exceed 20 ns.
2. Input undershoot voltage should be greater than –2 V and not exceed 20 ns.

Capacitance

Parameter	Symbol	Test Condition	Max	Unit
Input Capacitance	C_{IN}	V_{IN} = 0 V	10	pF
Output Capacitance	C_{OUT}	V_{OUT} = 0 V	7	pF

Notes:
1. Tested at T_A = 25°C, f = 1 MHz
2. These parameters are sampled and are not 100% tested

DC I/O Pin Characteristics

Parameter	Symbol	Test Conditions	Min	Max
Input Leakage Current	I_{IL}	V_{IN} = 0 to V_{DD}	–2 uA	2 uA
Output Leakage Current	I_{OL}	Output High Z, V_{OUT} = 0 to V_{DD}	–1 uA	1 uA
Output High Voltage	V_{OH}	I_{OH} = –4 mA	2.4	
Output Low Voltage	V_{OL}	I_{OL} = +4 mA		0.4 V

Power Supply Currents

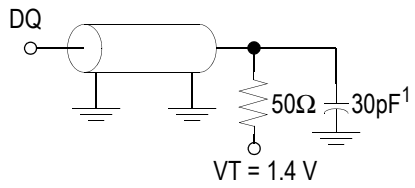
Parameter	Symbol	Test Conditions	0 to 70°C			–40 to 85°C		
			8 ns	10 ns	12 ns	8 ns	10 ns	12 ns
Operating Supply Current	I_{DD}	$\overline{E} \le V_{IL}$ All other inputs $\ge V_{IH}$ or $\le V_{IL}$ Min. cycle time I_{OUT} = 0 mA	160 mA	130 mA	115 mA	180 mA	150 mA	135 mA
Standby Current	I_{SB1}	$\overline{E} \ge V_{IH}$ All other inputs $\ge V_{IH}$ or $\le V_{IL}$ Min. cycle time	60 mA	50 mA	50 mA	80 mA	70 mA	70 mA
Standby Current	I_{SB2}	$E \ge V_{DD}$ - 0.2V All other inputs $\ge V_{DD}$ - 0.2V or $\le$ 0.2V	20 mA			40 mA		

AC Test Conditions

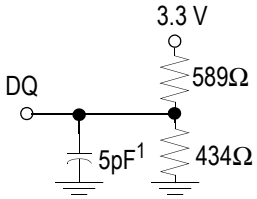
Parameter	Conditions
Input high level	V_{IH} = 2.4 V
Input low level	V_{IL} = 0.4 V
Input rise time	tr = 1 V/ns
Input fall time	tf = 1 V/ns
Input reference level	1.4 V
Output reference level	1.4 V
Output load	**Fig. 1& 2**

Notes:
1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown in **Fig. 1** unless otherwise noted
3. Output load 2 for t_{LZ}, t_{HZ}, t_{OLZ} and t_{OHZ}.

Output Load 1



Output Load 2

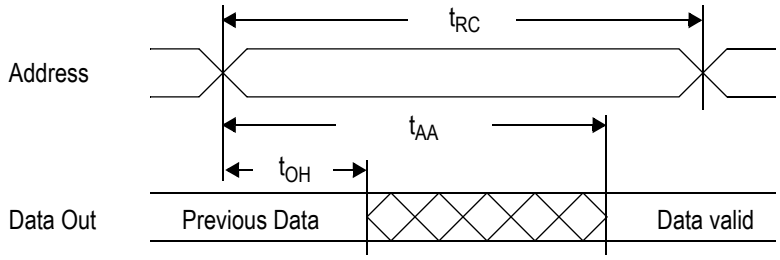


AC Characteristics

Read Cycle

Parameter	Symbol	-8		-10		-12		Unit
		Min	Max	Min	Max	Min	Max	
Read cycle time	t_{RC}	8	—	10	—	12	—	ns
Address access time	t_{AA}	—	8	—	10	—	12	ns
Chip enable access time ($\overline{CE}$)	t_{AC}	—	8	—	10	—	12	ns
Output enable to output valid ($\overline{OE}$)	t_{OE}	—	3.5	—	4	—	5	ns
Output hold from address change	t_{OH}	3	—	3	—	3	—	ns
Chip enable to output in low Z ($\overline{CE}$)	t_{LZ}*	3	—	3	—	3	—	ns
Output enable to output in low Z ($\overline{OE}$)	t_{OLZ}*	0	—	0	—	0	—	ns
Chip disable to output in High Z ($\overline{CE}$)	t_{HZ}*	—	4	—	5	—	6	ns
Output disable to output in High Z ($\overline{OE}$)	t_{OHZ}*	—	3.5	—	4	—	5	ns

Read Cycle 1: $\overline{CE}$ = $\overline{OE}$ = V_{IL}

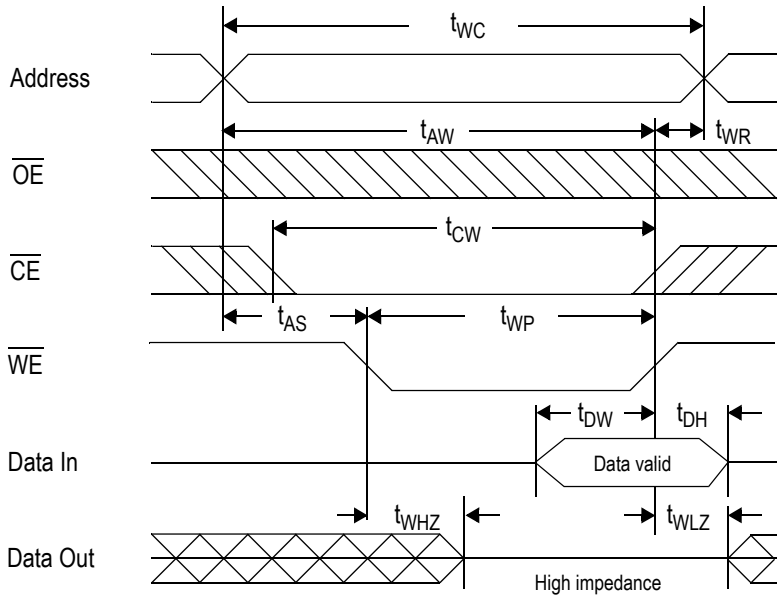


* These parameters are sampled and are not 100% tested

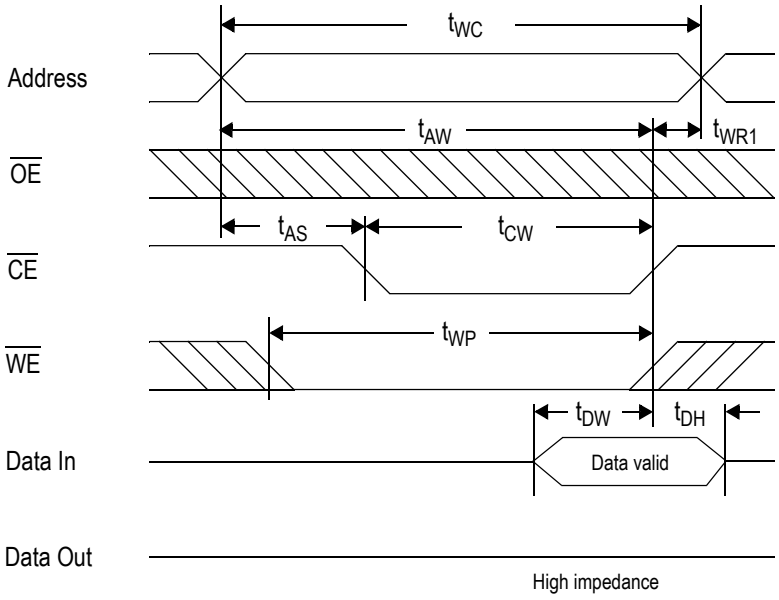
Write Cycle

Parameter	Symbol	-8		-10		-12		Unit
		Min	Max	Min	Max	Min	Max	
Write cycle time	tWC	8	—	10	—	12	—	ns
Address valid to end of write	tAW	5.5	—	7	—	8	—	ns
Chip enable to end of write	tCW	5.5	—	7	—	8	—	ns
Data set up time	tDW	4	—	5	—	6	—	ns
Data hold time	tDH	0	—	0	—	0	—	ns
Write pulse width	tWP	5.5	—	7	—	8	—	ns
Address set up time	tAS	0	—	0	—	0	—	ns
Write recovery time ($\overline{WE}$)	tWR	0	—	0	—	0	—	ns
Write recovery time ($\overline{CE}$)	tWR1	0	—	0	—	0	—	ns
Output Low Z from end of write	tWLZ*	3	—	3	—	3	—	ns
Write to output in High Z	tWHZ*	—	3.5	—	4	—	5	ns

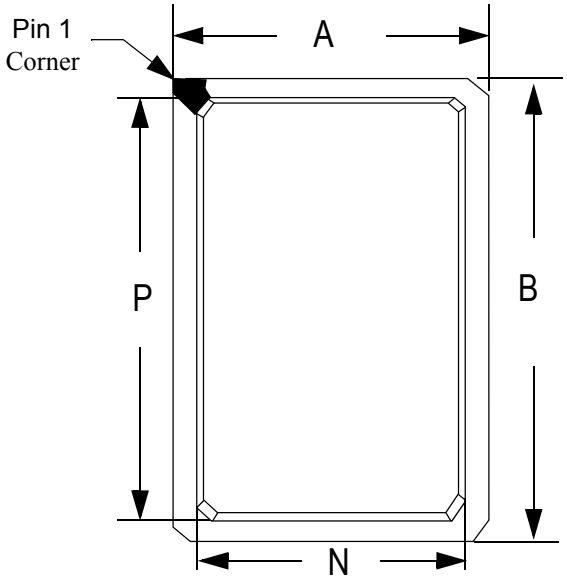
Write Cycle 1: $\overline{WE}$ Controlled



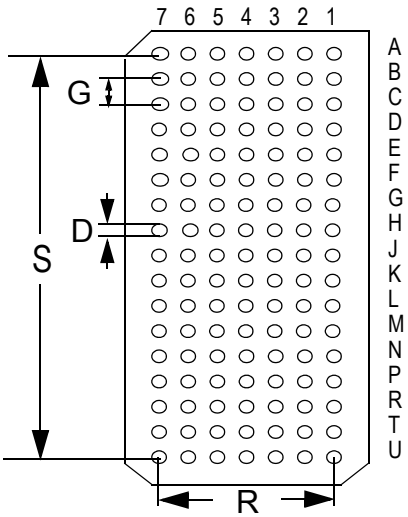
Write Cycle 2: $\overline{CE}$ Controlled



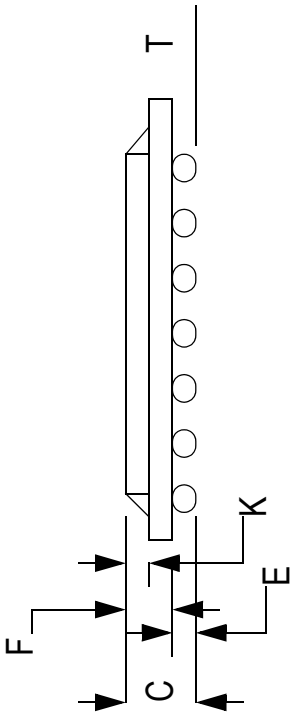
Package Dimensions - 119-bump PBGA



Top View



Bottom View



Side View

Package Dimensions - 119 Pin PBGA

Symbol	Description	Min.	Nom.	Max
A	Width	13.8	14.0	14.2
B	Length	21.8	22.0	22.2
C	Package Height (including ball)	-		2.40
D	Ball Size	0.60	0.75	0.90
E	Ball Height	0.50	0.60	0.70
F	Package Height (excluding balls)		1.46	1.70
G	Width between Balls		1.27	
K	Package Height above board	0.80	0.90	1.00
N	Cut-out Package Width		12.00	
P	Foot Length		19.50	
R	Width of package between balls		7.62	
S	Length of package between balls		20.32	
T	Variance of Ball Height		0.15	

Unit: mm

BPR 1999.05.18

Ordering Information

Part Number*	Package	Access Time	Temp. Range	Status
GS78108AB-8	BGA	8 ns	Commercial	
GS78108AB-10	BGA	10 ns	Commercial	
GS78108AB-12	BGA	12 ns	Commercial	
GS78108AB-8I	BGA	8 ns	Industrial	
GS78108AB-10I	BGA	10 ns	Industrial	
GS78108AB-12I	BGA	12 ns	Industrial	
GS78108AB-15I	BGA	15 ns	Industrial	

* Customers requiring delivery in Tape and Reel should add the character "T" to the end of the part number. For example: GS78108AB-12T

Revision History

Rev. Code: Old; New	Types of Changes Format or Content	Page #/Revisions/Reason
GS78108AB_r1		• Creation of new datasheet

